



ATP602

N-Channel Power MOSFET 600V, 5A, 2.7Ω, ATPAK

ON Semiconductor®
<http://onsemi.com>

Features

- ON-resistance $R_{DS(on)}=2.1\Omega$ (typ.)
- 10V drive
- Input capacitance $C_{iss}=350\text{pF}$ (typ.)
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		600	V
Gate-to-Source Voltage	V_{GSS}		± 30	V
Drain Current (DC)	I_D		5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	15	A
Allowable Power Dissipation	P_D	$T_c=25^\circ\text{C}$	70	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *1	E_{AS}		74	mJ
Avalanche Current *2	I_{AV}		5	A

 Note : *1 $V_{DD}=99\text{V}$, $L=5\text{mH}$, $I_{AV}=5\text{A}$ (Fig.1)

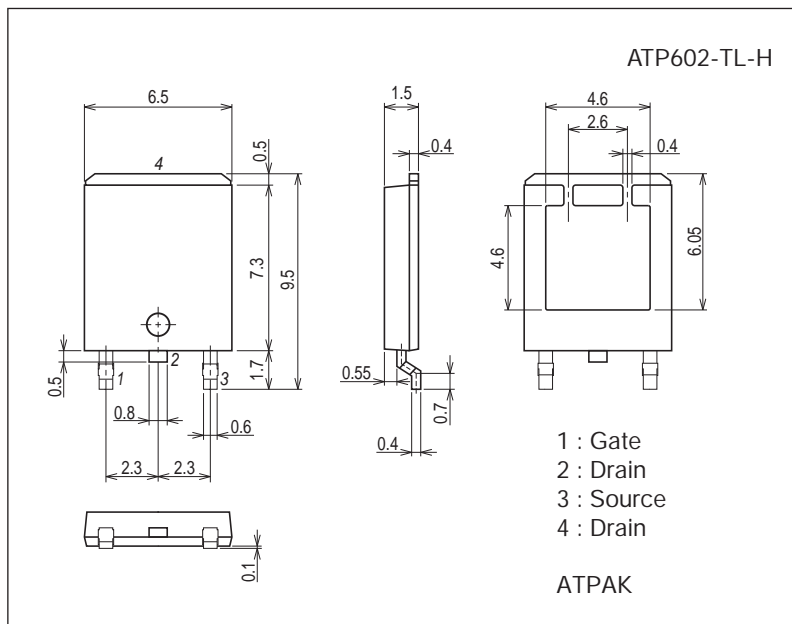
 *2 $L \leq 5\text{mH}$, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

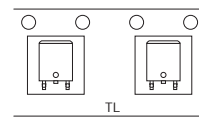
7057-001



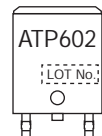
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

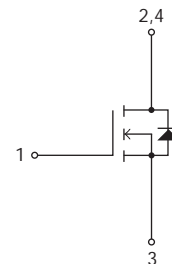
Packing Type: TL



Marking



Electrical Connection



ATP602

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
			min	typ	max		
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =10mA, V _{GS} =0V	600			V	
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =480V, V _{GS} =0V			100	μA	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =2.5A	1.5	2.9		S	
Static Drain-to-Source On-State Resistance	R _{DS(on)}	I _D =2.5A, V _{GS} =10V		2.1	2.7	Ω	
Input Capacitance	C _{iss}	V _{DS} =30V, f=1MHz		350		pF	
Output Capacitance	C _{oss}				68		pF
Reverse Transfer Capacitance	C _{rss}				15		pF
Turn-ON Delay Time	t _{d(on)}	See Fig.2		14.2		ns	
Rise Time	t _r			37.4		ns	
Turn-OFF Delay Time	t _{d(off)}			36.2		ns	
Fall Time	t _f			20.4		ns	
Total Gate Charge	Q _g	V _{DS} =200V, V _{GS} =10V, I _D =5A		13.6		nC	
Gate-to-Source Charge	Q _{gs}			3.4		nC	
Gate-to-Drain "Miller" Charge	Q _{gd}			7.2		nC	
Diode Forward Voltage	V _{SD}	I _S =5A, V _{GS} =0V		0.9	1.2	V	

Fig.1 Avalanche Resistance Test Circuit

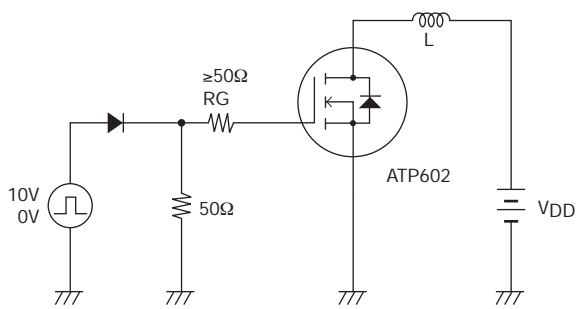
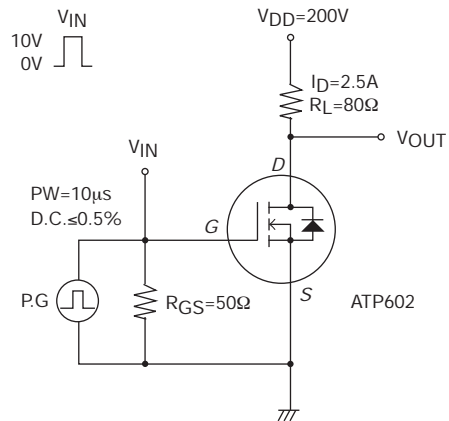
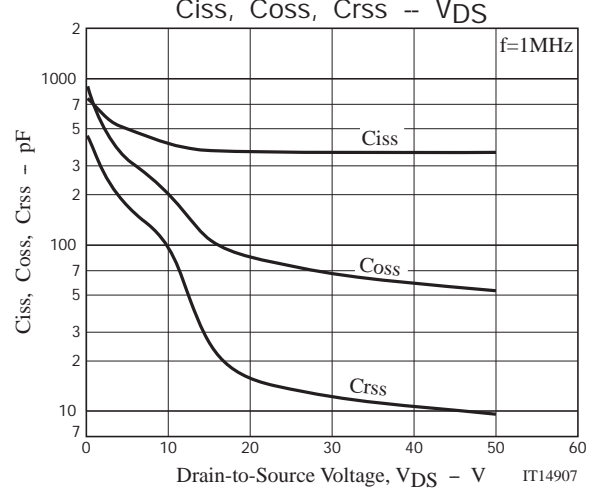
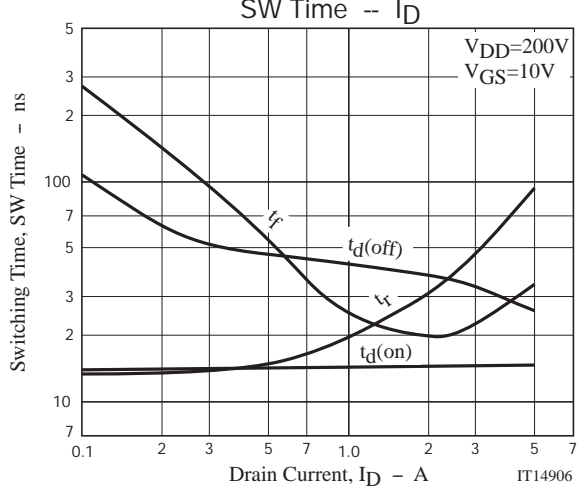
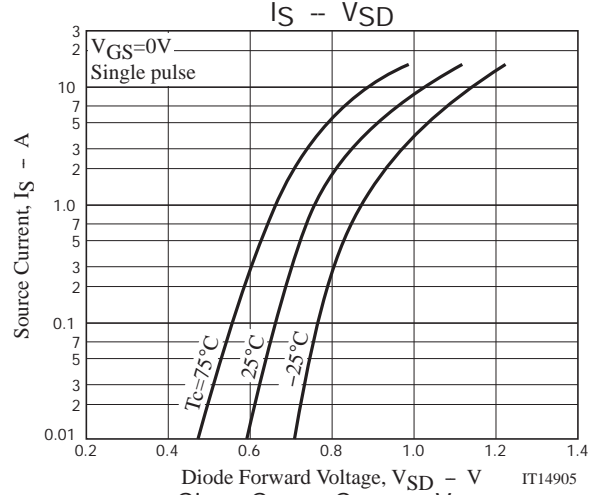
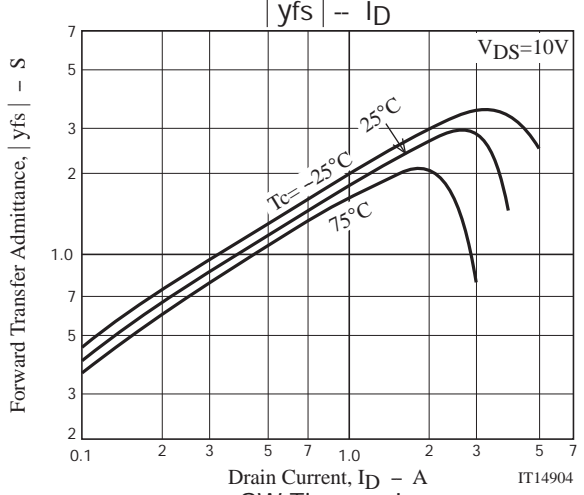
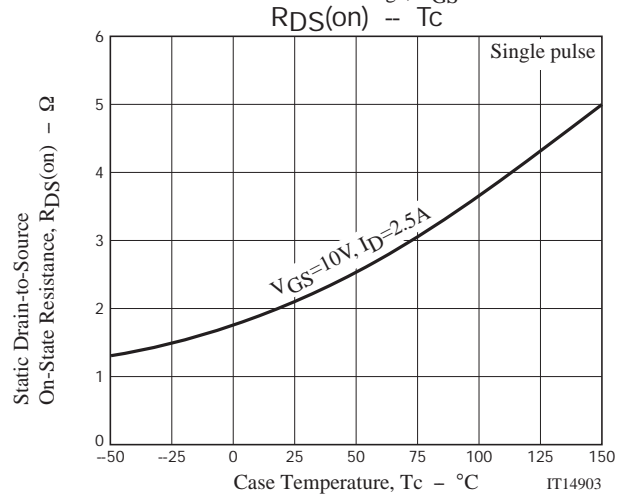
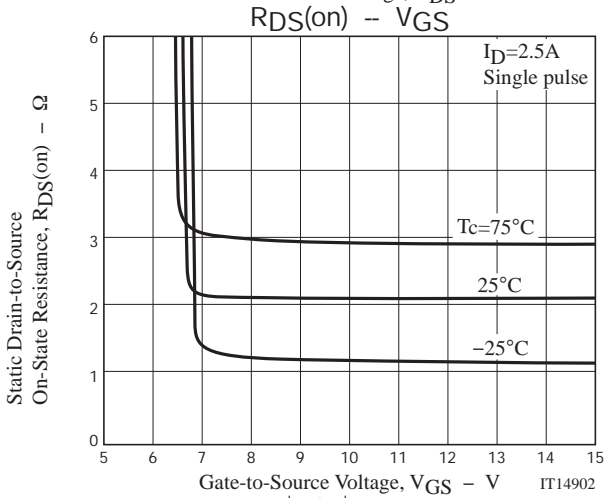
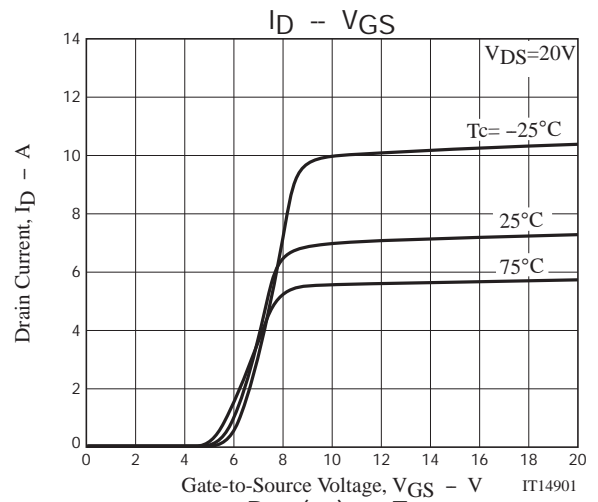
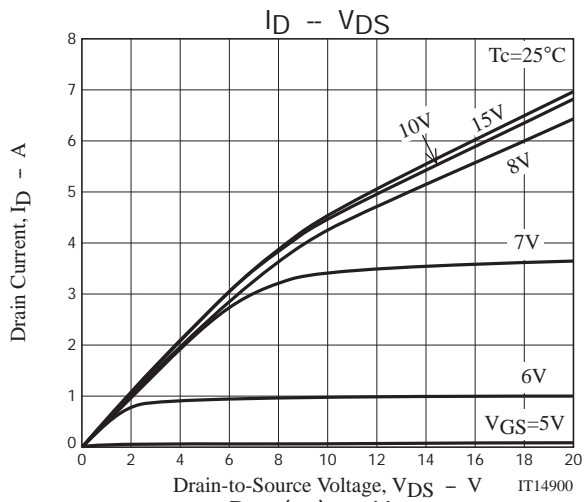


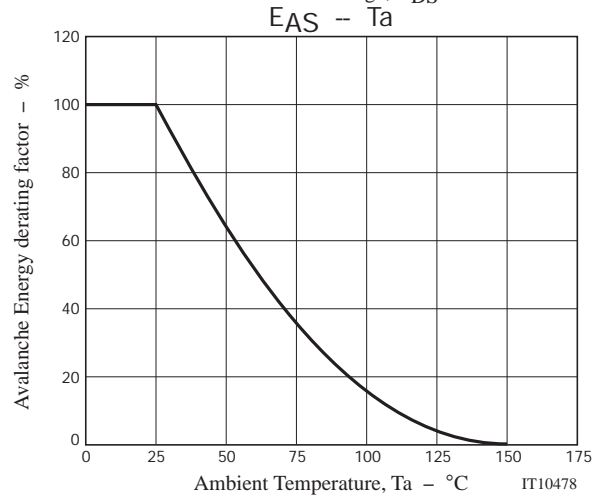
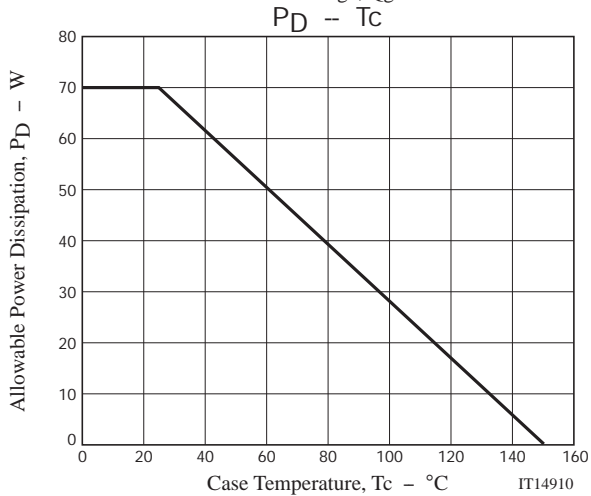
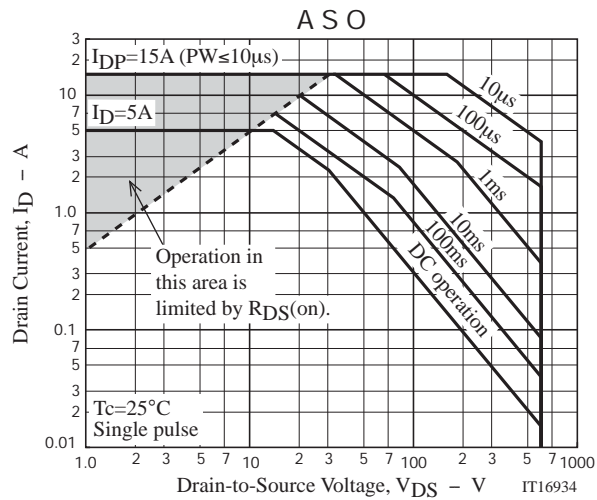
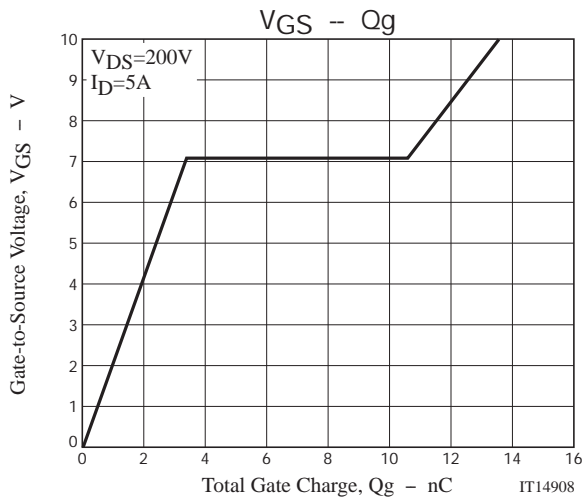
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP602-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free





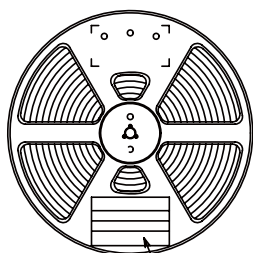
Taping Specification

ATP602-TL-H

1. Packing Format (TL)

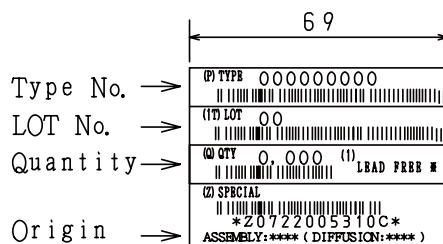
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

Packing method



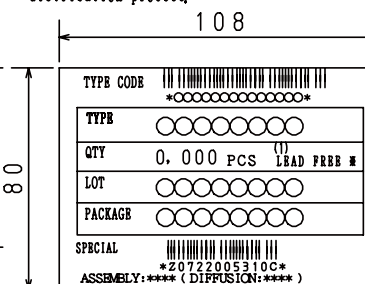
Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



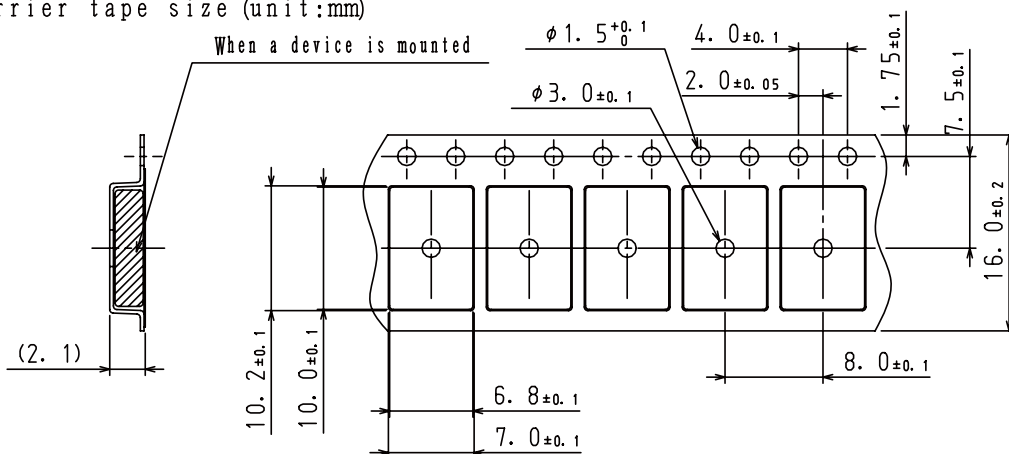
NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

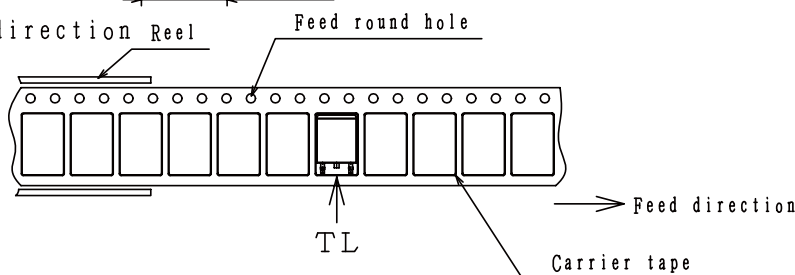
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction Reel



The one electrode terminals on feed hole side...TL

ATP602

Outline Drawing

ATP602-TL-H



Land Pattern Example



Note on usage : Since the ATP602 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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